



1200V SiC Schottky Diode

| VDC | 1200 V |
|---------------------|--------|
| Q _c | 86 nC |
| I _F | 15 A |
| T _j ,max | 175 °C |

Amp+[™] Features

- Unipolar rectifier with surge current
- Zero reverse recovery current
- · Fast, temperature-independent switching
- Avalanche tested to 200mJ*
- All parts tested to greater than 1,400V

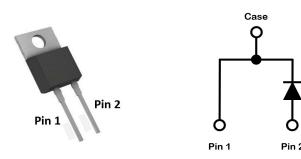
Amp+[™] Benefits

- Near zero switching loss
- Higher efficiency
- Smaller heat sink
- Easy to parallel

Amp+[™] Applications

- Solar Inverters
- · Switch mode power supplies, UPS
- Power factor correction
- EV charging stations

Package



| Part # | Package | Marking |
|--------------|-----------|-----------|
| GP3D015A120A | TO-220-2L | 3D015A120 |



Maximum Ratings, at T_i=25 °C, unless otherwise specified

| Characteristics | Symbol | Conditions | Values | Unit | |
|--|---------------------------------------|--|--------|--------------------|--|
| Continuous forward current | I _{F**} | T _C =25 °C, T _j =175 °C | 49 | | |
| | | T _C =125 °C, T _j =175 °C | 27 | А | |
| | | T _C =150 °C, T _j =175 °C | 18 | | |
| Surge non-repetitive forward current sine halfwave | _ | $T_{\rm C}$ =25 °C, $t_{\rm p}$ =8.3 ms | 150 | А | |
| | I _{FSM} | T _C =110 °C, t _p =8.3 ms | 120 | | |
| Non-repetitive peak forward current | I _{F,max} | T _C =25 °C, t _p =10 μs | 900 | Α | |
| i^2t value | ∫i²dt | $T_{\rm C}$ =25 °C, $t_{\rm p}$ =8.3 ms | 93 | - A ² s | |
| | | T _C =110 °C, t _p =8.3 ms | 60 | | |
| Repetitive peak reverse voltage | V_{RRM} | T _j =25 °C | 1200 | V | |
| Diode dv/dt ruggedness | dv/dt | Turn-on slew rate, repetitive | 200 | V/ns | |
| Power dissipation | P _{tot**} | T _C =25 °C | 252 | W | |
| Operating junction & storage temperature | T _j , T _{storage} | Continuous | -55175 | °C | |
| Soldering temperature | T _{solder} | Wave soldering leads | 260 | °C | |
| Mounting torque | | M3 Screw | 1 | N-m | |

Notes:

^{*} EAS of 200 mJ is based on starting Tj = 25° C, L = 1.0 mH, IAS = 20.00 A, V = 50 V.

^{**} Typical Rth_{JC} used

$Amp + ^{TM}$

Electrical Characteristics, at T_j=25 °C, unless otherwise specified

| Characteristics | Symbol | Conditions | Values | | | Unit |
|-------------------------|-----------------|--|--------|------|------|------|
| | Syllibol | | min. | typ. | max. | Onit |
| DC blocking voltage | V _{DC} | T _j =25 °C | 1200 | - | - | V |
| Breakdown voltage | V _{BR} | I _R =1.00mA, T _j =25 °C | 1400 | - | - | V |
| Diode forward voltage | | I _F =15A, T _j =25 °C | - | 1.48 | 1.60 | V |
| | V _F | I _F =15A, T _j =125 °C | - | 1.79 | - | |
| | | I _F =15A, T _j =175 °C | - | 2.10 | 2.70 | |
| Reverse current | I _R | V _R =1,200V, T _j =25 °C | - | 1 | 30 | - μΑ |
| | | V _R =1,400V, T _j =25 °C | - | 6 | - | |
| | | V _R =1,200V, T _j =125 °C | - | 10 | - | |
| | | V _R =1,200V, T _j =175 °C | - | 41 | 450 | |
| Total capacitive charge | Q _C | V _R =800V, T _j =25 °C | - | 86 | - | nC |
| Total capacitance | | V _R =1V, f=1 MHz | - | 962 | - | pF |
| | С | V _R =400V, f=1 MHz | - | 81 | - | |
| | | V _R =800V, f=1 MHz | - | 59 | - | |

Thermal Characteristics

| Characteristics Symbol | Symbol | Conditions | Values | | | Unit |
|-----------------------------------|-------------------|------------|--------|------|------|-------|
| | Syllibol | | min. | typ. | max. | Ollit |
| Thermal resistance, junction-case | R _{thJC} | - | - | 0.60 | 0.74 | °C/W |

Typical Performance

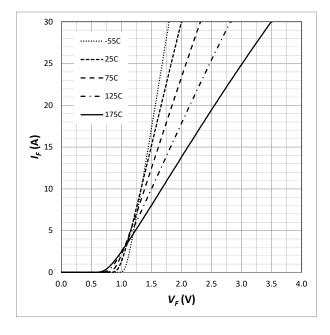


Fig. 1 Forward Characteristics (parameterized on T_i)

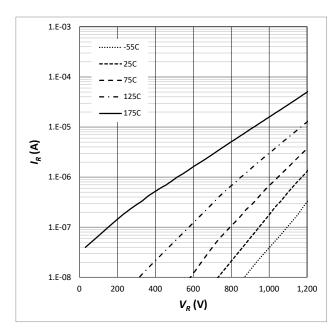
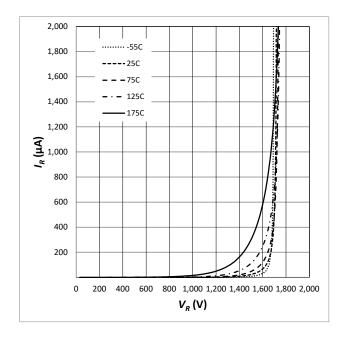


Fig. 2 Reverse Characteristics (parameterized on T_i)



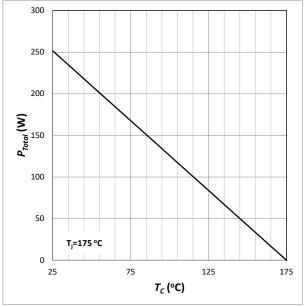
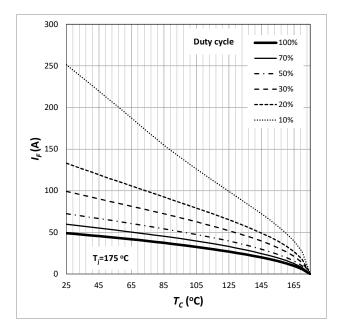


Fig. 3 Reverse Characteristics (parameterized on Tj)

Fig. 4 Power Derating





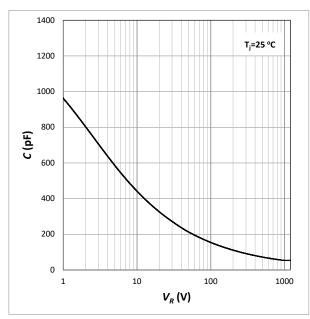
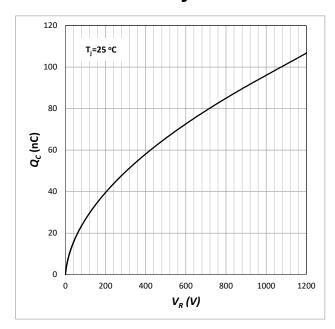


Fig. 6 Capacitance



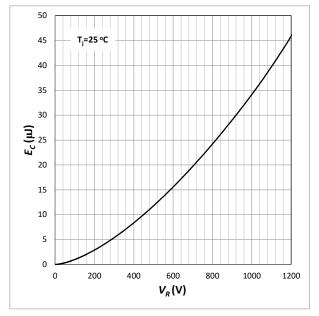


Fig. 7 Capacitive Charge

Fig. 8 Typical Capacitance Stored Energy

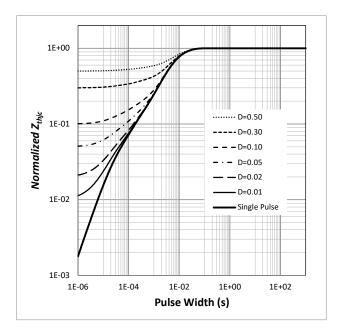
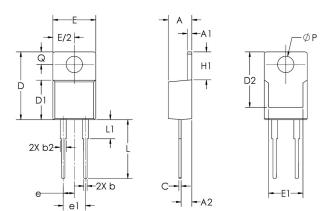


Fig. 9 Transient Thermal Impedance

Package Dimensions TO-220-2L



| Sum. | Millin | neters | Inches | | |
|------|----------|--------|--------|-------|--|
| Sym | Min | Max | Min | Max | |
| Α | 3.56 | 4.83 | 0.140 | 0.190 | |
| A1 | 0.51 | 1.40 | 0.020 | 0.055 | |
| A2 | 2.03 | 2.92 | 0.080 | 0.115 | |
| b | 0.38 | 1.02 | 0.015 | 0.040 | |
| b2 | 1.02 | 1.78 | 0.040 | 0.070 | |
| С | 0.36 | 0.76 | 0.014 | 0.030 | |
| D | 14.22 | 16.51 | 0.560 | 0.650 | |
| D1 | 8.38 | 9.40 | 0.330 | 0.370 | |
| D2 | 12.19 | 13.13 | 0.480 | 0.517 | |
| E | 9.65 | 10.67 | 0.380 | 0.420 | |
| E1 | 6.86 | 8.89 | 0.270 | 0.350 | |
| е | 2.54 BSC | | .100 | BSC | |
| e1 | 5.08 | BSC | .200 | BSC | |
| H1 | 5.84 | 6.86 | 0.230 | 0.270 | |
| L | 12.57 | 14.73 | 0.495 | 0.580 | |
| L1 | 3.60 | 6.35 | 0.142 | 0.250 | |
| ØP | 3.53 | 4.09 | 0.139 | 0.161 | |
| Q | 2.54 | 3.43 | 0.100 | 0.135 | |

Notes

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

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